# **Complementary Silicon Plastic Power Transistors**

Designed for use in general purpose amplifier and switching applications.

#### **Features**

• ESD Ratings: Machine Model, C; > 400 V

Human Body Model, 3B; > 8000 V

• Epoxy Meets UL 94 V-0 @ 0.125 in

• Pb-Free Packages are Available\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage TIP41, TIP42 TIP41A, TIP42A TIP41B, TIP42B TIP41C, TIP42C	V <sub>CEO</sub>	40 60 80 100	Vdc
Collector-Base Voltage TIP41, TIP42 TIP41A, TIP42A TIP41B, TIP42B TIP41C, TIP42C	V <sub>CB</sub>	40 60 80 100	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5.0	Vdc
Collector Current- Continuous Peak	IC	6.0 10	Adc
Base Current	Ι <sub>Β</sub>	2.0	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	65 0.52	W W/°C
Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	2.0 0.016	W W/°C
Unclamped Inductive Load Energy (Note 1)	Е	62.5	mJ
Operating and Storage Junction, Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	—65 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.67	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	57	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

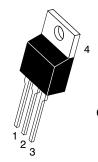
1.  $I_C = 2.5 \text{ A}, L = 20 \text{ mH}, P.R.F. = 10 \text{ Hz}, V_{CC} = 10 \text{ V}, R_{BE} = 100 \Omega.$ 



#### ON Semiconductor®

http://onsemi.com

# 6 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 40-60-80-100 VOLTS, 65 WATTS



MARKING DIAGRAM

TO-220AB CASE 221A STYLE 1



TIP4xx = Device Code xx = 1, 1A, 1B, 1C 2, 2A, 2B, 2C A = Assembly Location Y = Year

Y = Year WW = Work Week G = Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	•	•
Collector-Emitter Sustaining Voltage (Note 2) $(I_C = 30 \text{ mAdc}, I_B = 0)$	TIP41, TIP42 TIP41A, TIP42A TIP41B, TIP42B TIP41C, TIP42C	V <sub>CEO(sus)</sub>	40 60 80 100	- - -	Vdc
Collector Cutoff Current $(V_{CE} = 30 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 60 \text{ Vdc}, I_B = 0)$	TIP41, TIP41A, TIP42, TIP42A TIP41B, TIP41C, TIP42B, TIP42C	I <sub>CEO</sub>	- -	0.7 0.7	mAdc
Collector Cutoff Current $ (V_{CE} = 40 \text{ Vdc}, V_{EB} = 0) $ $ (V_{CE} = 60 \text{ Vdc}, V_{EB} = 0) $ $ (V_{CE} = 80 \text{ Vdc}, V_{EB} = 0) $ $ (V_{CE} = 100 \text{ Vdc}, V_{EB} = 0) $	TIP41, TIP42 TIP41A, TIP42A TIP41B, TIP42B TIP41C, TIP42C	I <sub>CES</sub>	- - - -	400 400 400 400	μAdc
Emitter Cutoff Current ( $V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0$ )		I <sub>EBO</sub>	-	1.0	mAdc
ON CHARACTERISTICS (Note 2)					
DC Current Gain (I <sub>C</sub> = 0.3 Adc, $V_{CE}$ = 4.0 Vdc) (I <sub>C</sub> = 3.0 Adc, $V_{CE}$ = 4.0 Vdc)		h <sub>FE</sub>	30 15	- 75	-
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 6.0 Adc, I <sub>B</sub> = 600 mAdc)		V <sub>CE(sat)</sub>	-	1.5	Vdc
Base-Emitter On Voltage (I <sub>C</sub> = 6.0 Adc, V <sub>CE</sub> = 4.0 Vdc)		V <sub>BE(on)</sub>	-	2.0	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain — Bandwidth Product (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz)		f <sub>T</sub>	3.0	-	MHz
Small-Signal Current Gain (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)		h <sub>fe</sub>	20	-	-

<sup>2.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

#### **ORDERING INFORMATION**

Device	Package	Shipping
TIP41	TO-220	50 Units / Rail
TIP41G	TO-220 (Pb-Free)	50 Units / Rail
TIP41A	TO-220	50 Units / Rail
TIP41AG	TO-220 (Pb-Free)	50 Units / Rail
TIP41B	TO-220	50 Units / Rail
TIP41BG	TO-220 (Pb-Free)	50 Units / Rail
TIP41C	TO-220	50 Units / Rail
TIP41CG	TO-220 (Pb-Free)	50 Units / Rail
TIP42	TO-220	50 Units / Rail
TIP42G	TO-220 (Pb-Free)	50 Units / Rail
TIP42A	TO-220	50 Units / Rail
TIP42AG	TO-220 (Pb-Free)	50 Units / Rail
TIP42B	TO-220	50 Units / Rail
TIP42BG	TO-220 (Pb-Free)	50 Units / Rail
TIP42C	TO-220	50 Units / Rail
TIP42CG	TO-220 (Pb-Free)	50 Units / Rail

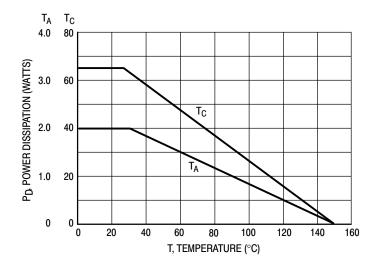
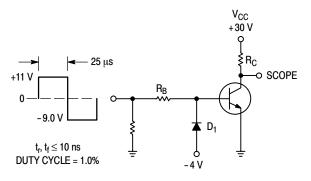


Figure 1. Power Derating



 $R_B$  and  $R_C$  VARIED TO OBTAIN DESIRED CURRENT LEVELS D<sub>1</sub> MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE I\_B  $\approx$  100 mA MSD6100 USED BELOW I\_B  $\approx$  100 mA

2.0  $T_J = 25^{\circ}C$ 1.0 V<sub>CC</sub> = 30 V 0.7  $I_{\rm C}/I_{\rm B} = 10$ 0.5 t, TIME (µs) 0.3 0.2 0.1 0.07  $t_d \ @ \ V_{BE(off)} \approx 5.0 \ V$ 0.05 0.03 0.02 0.06 0.1 0.4 0.6 1.0 2.0 4.0 6.0 I<sub>C</sub>, COLLECTOR CURRENT (AMP)

Figure 2. Switching Time Test Circuit

Figure 3. Turn-On Time

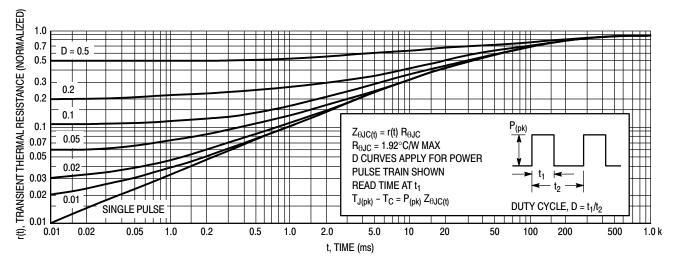


Figure 4. Thermal Response

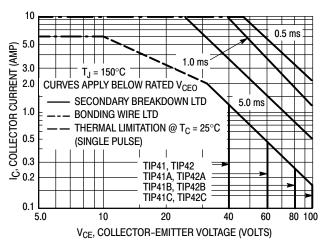


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C$  –  $V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

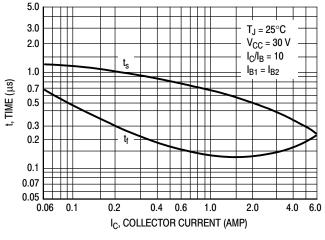


Figure 6. Turn-Off Time

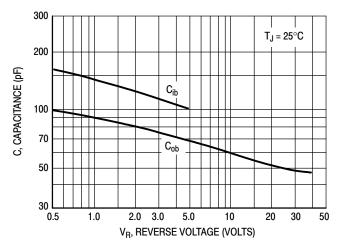


Figure 7. Capacitance

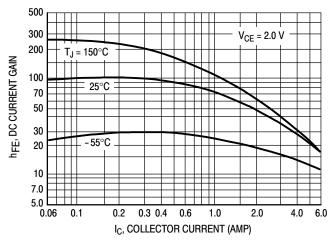


Figure 8. DC Current Gain

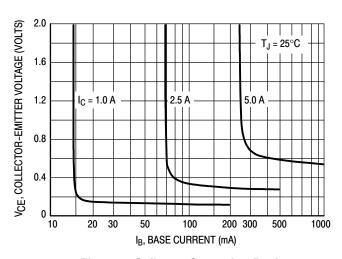


Figure 9. Collector Saturation Region

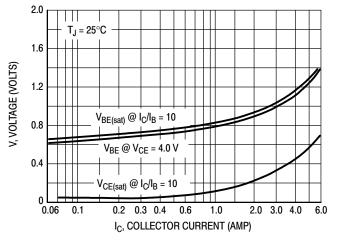


Figure 10. "On" Voltages

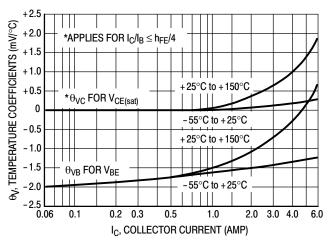


Figure 11. Temperature Coefficients

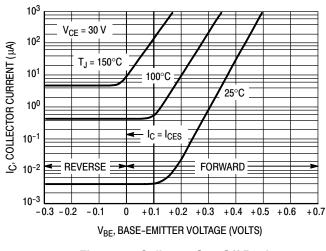


Figure 12. Collector Cut-Off Region

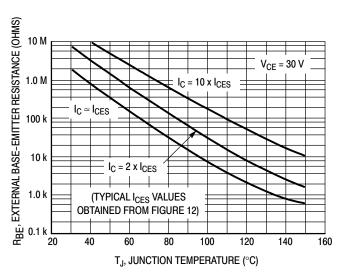
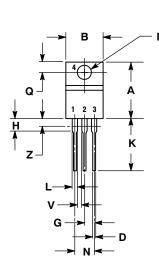
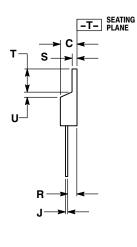


Figure 13. Effects of Base-Emitter Resistance

#### **PACKAGE DIMENSIONS**

**TO-220** CASE 221A-09 ISSUE AE





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
   THE TOTAL AND TOLERANCING PER ANSI
   TOLERANCIN
- Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

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